

P-Channel 8 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^d	Q_g (Typ.)
- 8	0.035 at $V_{GS} = - 4.5$ V	- 5.8	12 nC
	0.048 at $V_{GS} = - 2.5$ V	- 5.0	
	0.065 at $V_{GS} = - 1.8$ V	- 4.3	

FEATURES

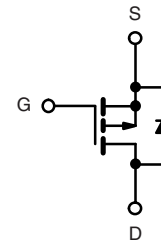
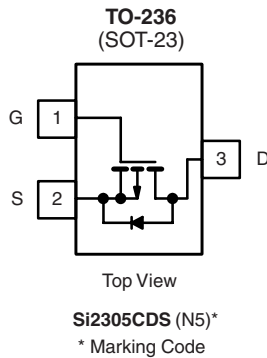
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices
- DC/DC Converter



P-Channel MOSFET

Ordering Information: Si2305CDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 8	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	- 5.8
		$T_C = 70$ °C	- 4.7
		$T_A = 25$ °C	- 4.4 ^{a, b}
		$T_A = 70$ °C	- 3.5 ^{a, b}
Pulsed Drain Current (10 μ s Pulse Width)	I_{DM}	- 20	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	- 0.8 ^{a, b}
Maximum Power Dissipation	P_D	$T_C = 25$ °C	1.7
		$T_C = 70$ °C	1.1
		$T_A = 25$ °C	0.96 ^{a, b}
		$T_A = 70$ °C	0.62 ^{a, b}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	R_{thJA}	100	130	°C/W	
Maximum Junction-to-Foot (Drain)	R_{thJF}	60	75		

Notes:

- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 175 °C/W.
- $T_C = 25$ °C.

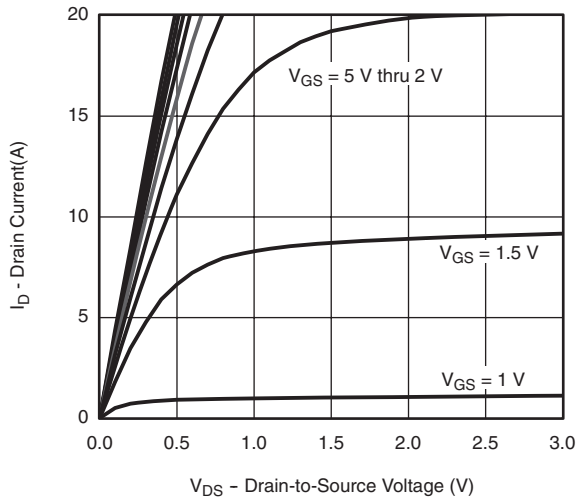
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	- 8			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		- 9		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$		2.5			
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	- 0.4		- 1	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$			- 1	μA
		$V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			- 10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	- 10			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -4.4\text{ A}$		0.028	0.035	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -3.8\text{ A}$		0.039	0.048	
		$V_{GS} = -1.8\text{ V}, I_D = -2\text{ A}$		0.053	0.065	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -4\text{ V}, I_D = -4.4\text{ A}$		17		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		960		pF
Output Capacitance	C_{oss}			330		
Reverse Transfer Capacitance	C_{rss}			300		
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -8\text{ V}, I_D = -4.4\text{ A}$		20	30	nC
Total Gate Charge	Q_g	$V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -4.4\text{ A}$		12	18	
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			3.1		
Gate Resistance	R_g	$f = 1\text{ MHz}$	1	5.1	10.2	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 1.1\text{ }\Omega$ $I_D \cong -3.5\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		20	30	ns
Rise Time	t_r			20	30	
Turn-Off Delay Time	$t_{d(off)}$			40	60	
Fall Time	t_f			10	15	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -4\text{ V}, R_L = 1.1\text{ }\Omega$ $I_D \cong -3.5\text{ A}, V_{GEN} = -8\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	t_r			10	15	
Turn-Off Delay Time	$t_{d(off)}$			35	55	
Fall Time	t_f			10	15	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			- 1.4	A
Pulse Diode Forward Current	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	$I_S = -3.5\text{ A}, V_{GS} = 0\text{ V}$		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -3.5\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		35	55	ns
Body Diode Reverse Recovery Charge	Q_{rr}			14	25	nC
Reverse Recovery Fall Time	t_a			16		ns
Reverse Recovery Rise Time	t_b			19		

Notes:

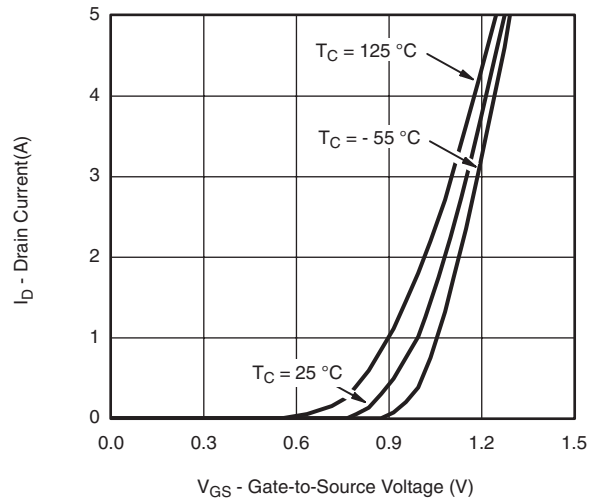
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

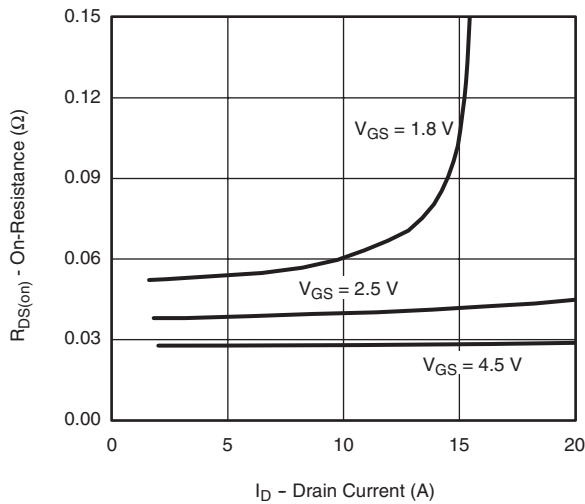
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



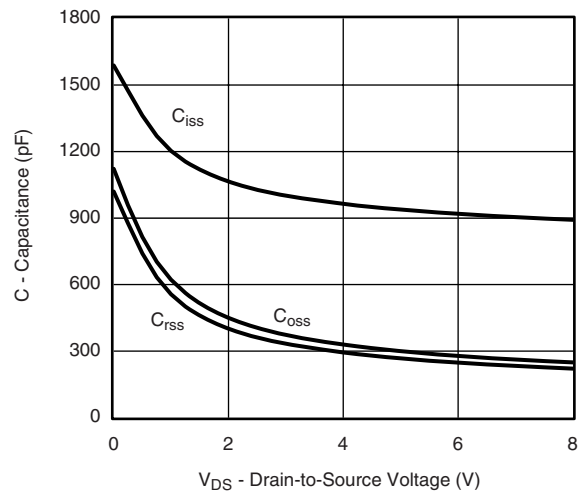
Output Characteristics



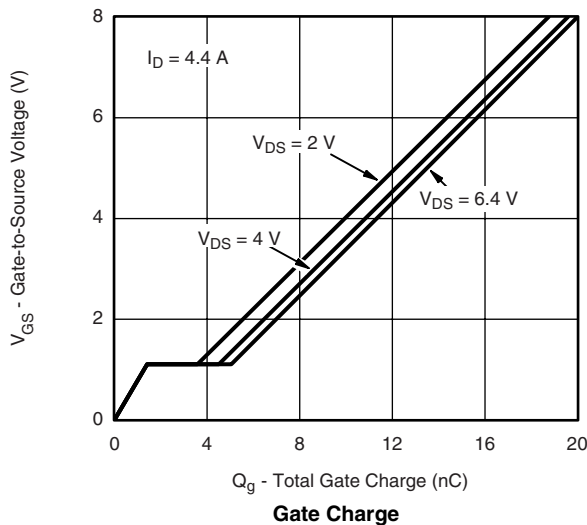
Transfer Characteristics



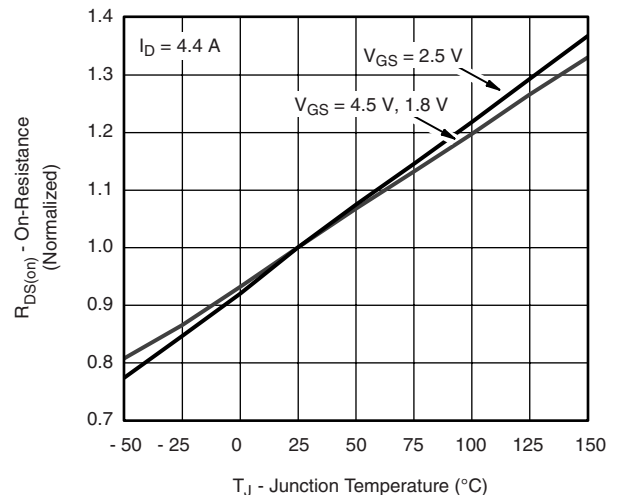
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

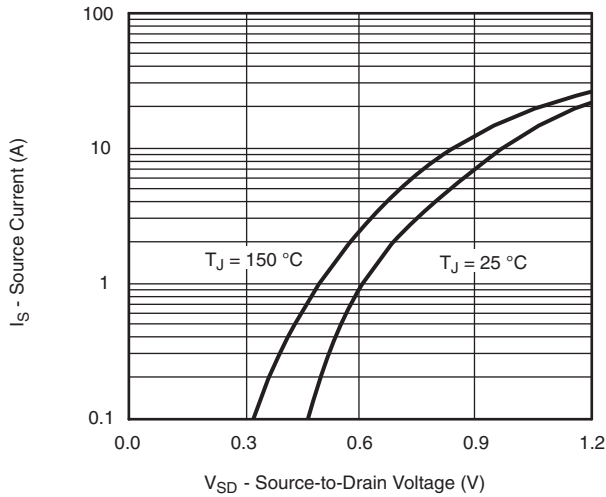


Gate Charge

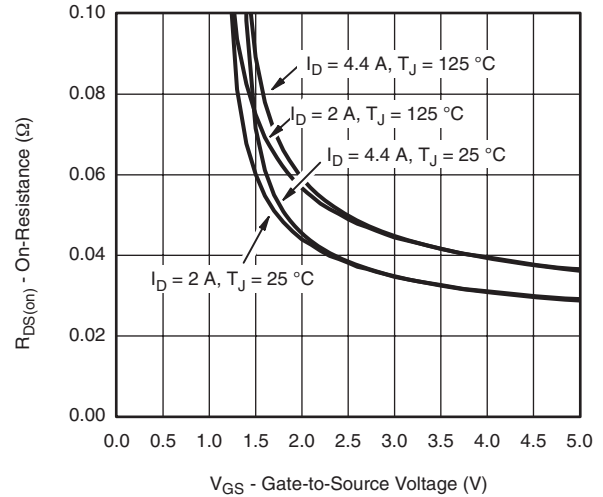


On-Resistance vs. Junction Temperature

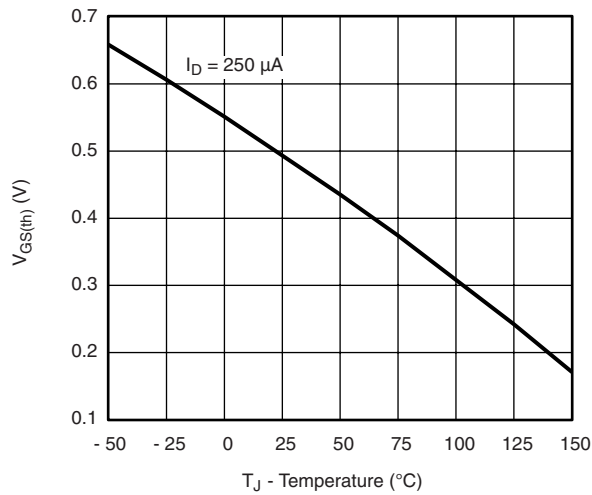
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



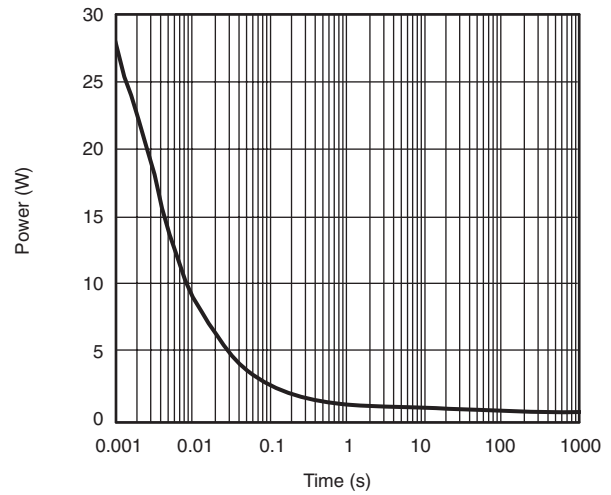
Source-Drain Diode Forward Voltage



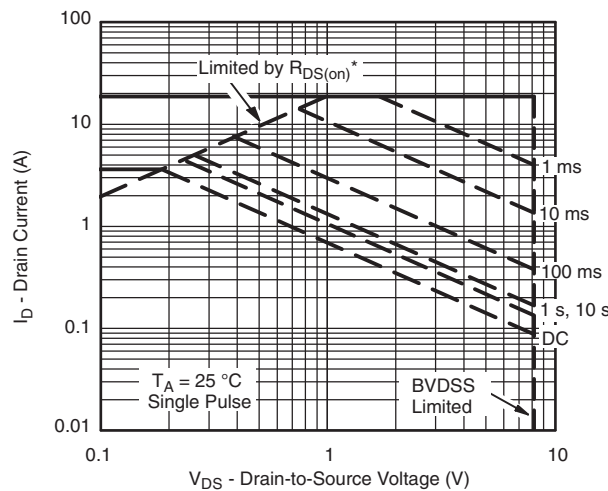
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



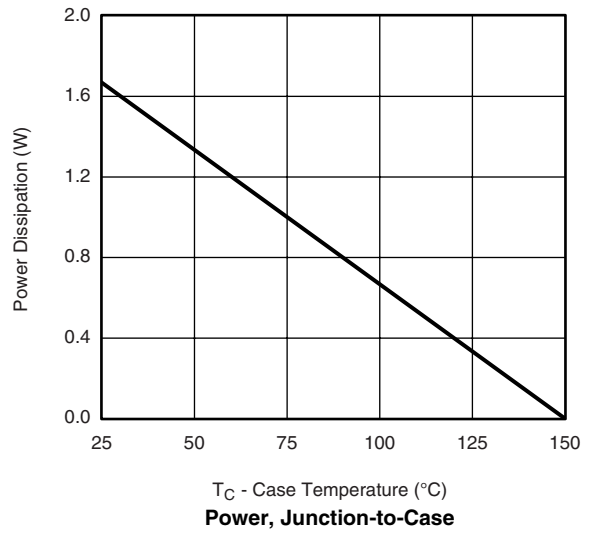
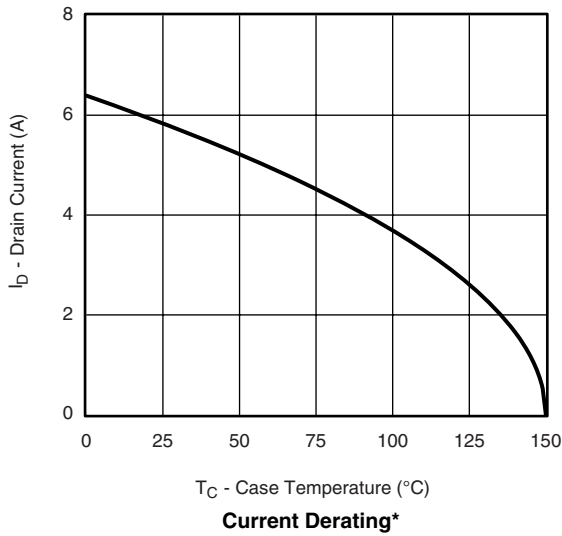
Single Pulse Power, Junction-to-Ambient



* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

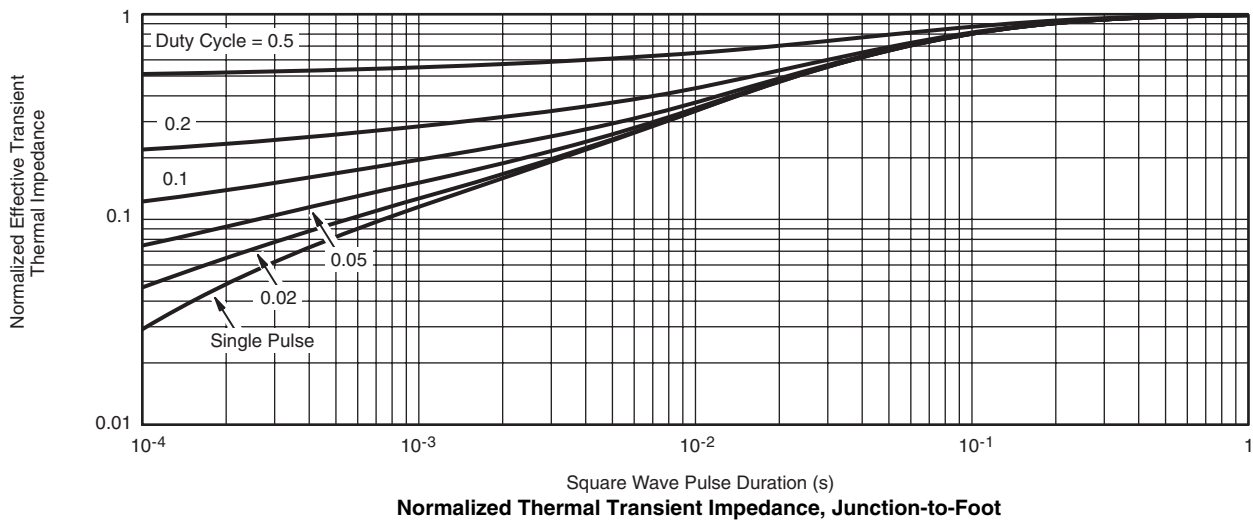
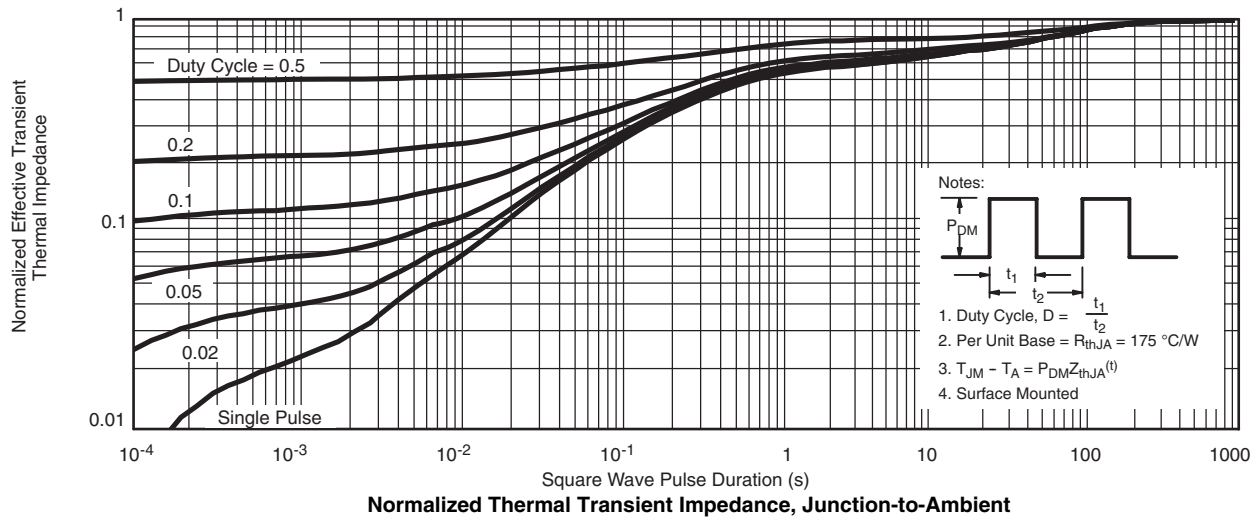
Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOT-23 (TO-236): 3-LEAD



Dim	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	0.89	1.12	0.035	0.044
A ₁	0.01	0.10	0.0004	0.004
A ₂	0.88	1.02	0.0346	0.040
b	0.35	0.50	0.014	0.020
c	0.085	0.18	0.003	0.007
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E ₁	1.20	1.40	0.047	0.055
e	0.95 BSC		0.0374 Ref	
e ₁	1.90 BSC		0.0748 Ref	
L	0.40	0.60	0.016	0.024
L ₁	0.64 Ref		0.025 Ref	
S	0.50 Ref		0.020 Ref	
q	3°	8°	3°	8°

ECN: S-03946-Rev. K, 09-Jul-01
 DWG: 5479

RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads
Dimensions in Inches/(mm)

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